

# PATENT ABSTRACTS OF JAPAN

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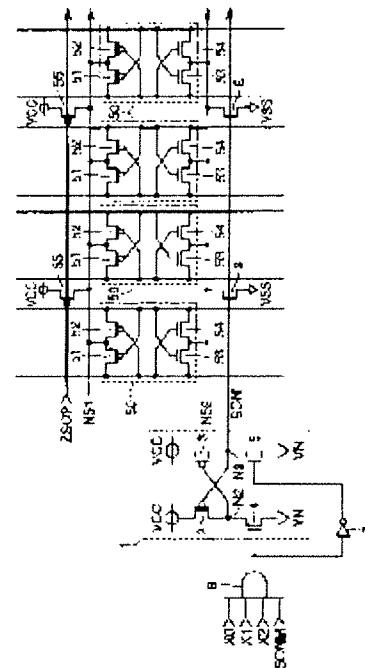
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## (54) SEMICONDUCTOR STORAGE DEVICE

### (57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a semiconductor storage device whose layout area is small and whose power consumption is small.

**SOLUTION:** In a DRAM, the channel length of an N channel MOS transistor 8 for giving ground potential VSS to a sense amplifier 50 to activate the amplifier 50 is made shorter than the channel lengths of N channel MOS transistors 53 and 54 included in the amplifier 50, and the gate potential of the transistor 8 in a standby mode is also made negative potential VN. Therefore, the layout area of the transistor 8 can be reduced and the leak current of the transistor 8 can be reduced.



## LEGAL STATUS

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